

L Number	Hits	Search Text	DB	Time stamp
1	16	susceptor and (sandblasting or blasted or blasting) and etch\$4 and (rinse or rinsing)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 14:56
2	25	susceptor same (sandblasting or blasted or blasting)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:21
3	91	susceptor and (sandblasting or blasted or blasting)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 15:22
4	8	(susceptor or chuck or pedestal) same (glass or "silicon dioxide" or "SiO.sub.2") same (sandblasting or blasted or blasting)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:16
5	329	(susceptor or chuck or pedestal) and (glass or "silicon dioxide" or "SiO.sub.2") and (sandblasting or blasted or blasting)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 15:24
6	160	((susceptor or chuck or pedestal) and (glass or "silicon dioxide" or "SiO.sub.2") and (sandblasting or blasted or blasting) ) and semiconductor	USPAT; EPO; JPO; IBM_TDB	2003/03/10 15:25
7	18	(susceptor or "substrate holder" or pedestal) and (glass or "silicon dioxide" or "SiO.sub.2") and (sandblasting or blasted or blasting) and etch\$4 and (rinse or rinsing)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:20
8	133	(susceptor or jig) same (sandblasting or blasted or blasting)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:28
9	2030	(susceptor or jig) same etch\$4	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:29
10	12	(susceptor or jig) same etch\$4 same blast\$3	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:31
11	32	(susceptor or jig) same etch\$4 same (rinse or rinsing)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:36
12	752	(SiC or "silicon carbide") same blast\$4	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:37
13	51	((SiC or "silicon carbide") same blast\$4) and (susceptor or jig)	USPAT; EPO; JPO; IBM_TDB	2003/03/10 16:37